

General Description

The AGM218MAP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

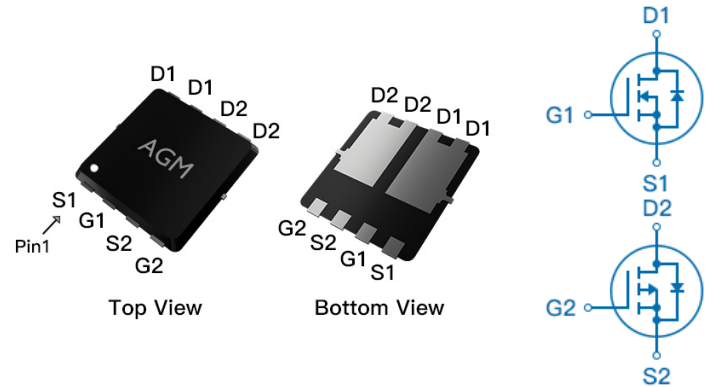
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
20V	16mΩ	20A
-20V	24mΩ	-19A

PDFN3.3*3.3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM218MAP	AGM218MAP	PDFN3.3*3.3	330mm	12mm	5000

Table 1. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	20	-20	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 12	± 12	V
I_D	Drain Current-Continuous($T_C=25^{\circ}\text{C}$) (Note 1)	20	-19	A
	Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	14	-13	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	80	-76	A
P_D	Total Power Dissipation($T_C=25^{\circ}\text{C}$)	35	35	W
	Total Power Dissipation($T_C=100^{\circ}\text{C}$)	14	14	W
EAS	Avalanche energy (Note 3)	20	42	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.6	$^{\circ}\text{C/W}$

Table 3. N- Channel Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	20	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=20V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±12V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	0.4	0.7	1.0	V
gFS	Forward Transconductance	VDS=5V,ID=3A	--	11	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=4.5V, ID=4A	--	16	20	mΩ
		VGS=2.5V, ID=3A	--	21	34	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=10V,VGS=0V, F=1MHZ	--	637	--	pF
Coss	Output Capacitance		--	135	--	pF
Crss	Reverse Transfer Capacitance		--	125	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=4.5V,VDS=10V, ID=4A,RGEN=6Ω	--	11	--	nS
tr	Turn-on Rise Time		--	30	--	nS
td(off)	Turn-Off Delay Time		--	35	--	nS
tf	Turn-Off Fall Time		--	10	--	nS
Qg	Total Gate Charge	VGS=4.5V, VDS=10V, ID=4A	--	11	--	nC
Qgs	Gate-Source Charge		--	1.2	--	nC
Qgd	Gate-Drain Charge		--	3.5	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	20	A
VSD	Forward on Voltage	VGS=0V,IS=4A	--	--	1.2	V
trr	Reverse Recovery Time	IF=4A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C,VDD=10V,Vgs=10V,ID=9A, L=0.5mH,RG=25ohm

Table 3. P-Channel Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-20	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-20V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±12V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-0.4	-0.7	-1.0	V
gFS	Forward Transconductance	VDS=-5V,ID=-3A	--	7	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-4.5V, ID=-4A	--	24	30	mΩ
		VGS=-2.5V, ID=-3A	--	33	43	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-10V,VGS=0V, F=1MHZ	--	673	--	pF
Coss	Output Capacitance		--	115	--	pF
Crss	Reverse Transfer Capacitance		--	109	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-10V, ID=-5A,RGEN=3Ω	--	15	--	nS
tr	Turn-on Rise Time		--	35	--	nS
td(off)	Turn-Off Delay Time		--	30	--	nS
tf	Turn-Off Fall Time		--	14	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-10V, ID=-5A	--	18	--	nC
Qgs	Gate-Source Charge		--	1.3	--	nC
Qgd	Gate-Drain Charge		--	2.5	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-19	A
VSD	Forward on Voltage	VGS=0V,IS=-4A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-4A , dI/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

3.EAS condition: TJ=25°C, VDD=-10V, Vgs=-10V, ID=-13A, L=0.5mH, RG=25ohm

N-Channel Typical Electrical and Thermal Characteristics

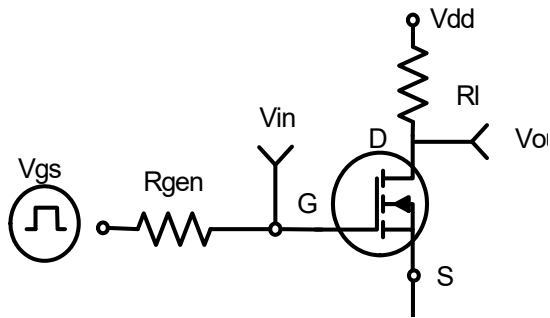


Figure 1: Switching Test Circuit

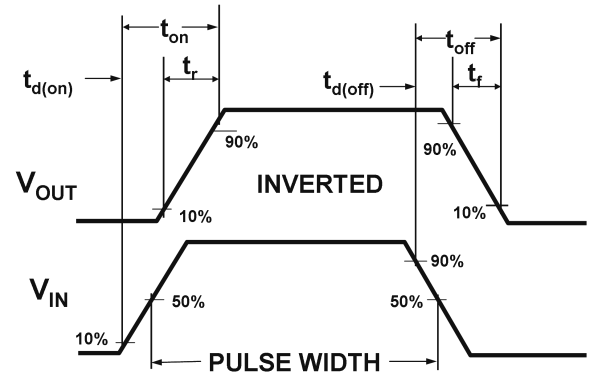


Figure 2: Switching Waveforms

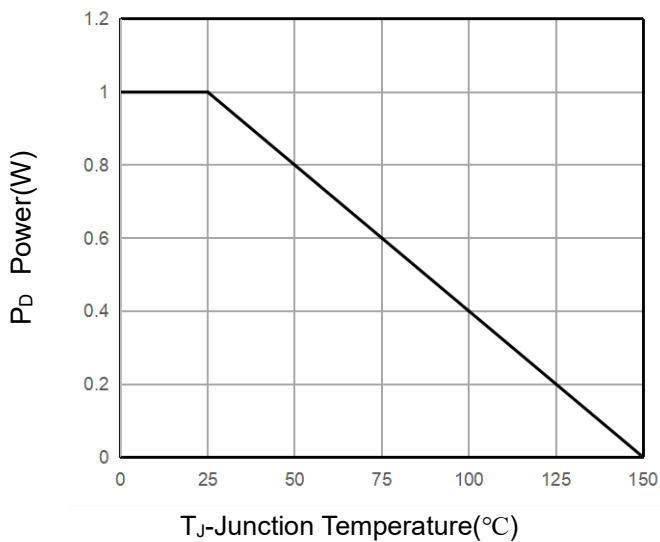


Figure 3 Power Dissipation

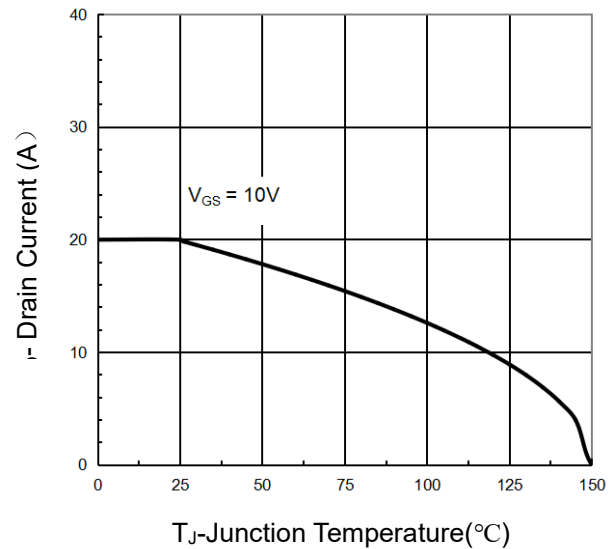


Figure 4 Drain Current

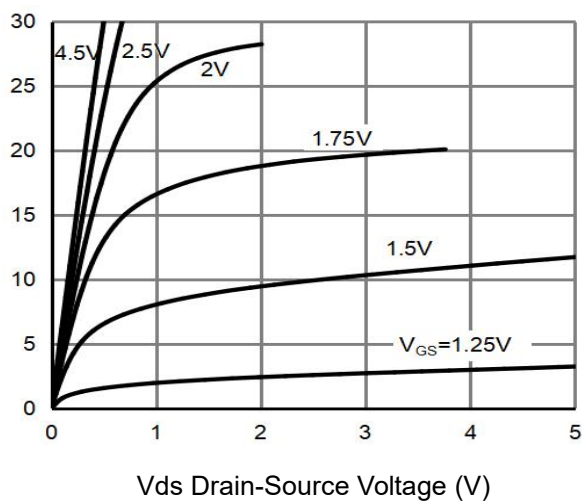


Figure 5 Output Characteristics

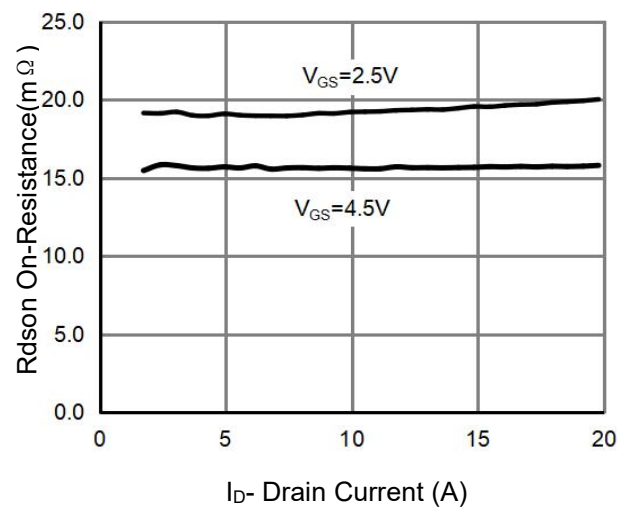


Figure 6 Drain-Source On-Resistance

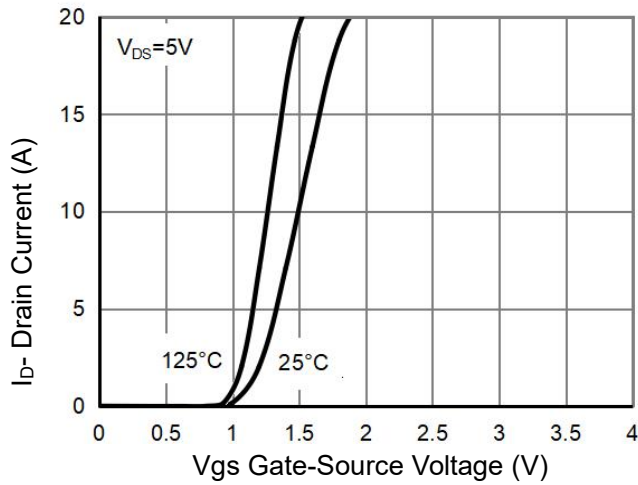


Figure 7 Transfer Characteristics

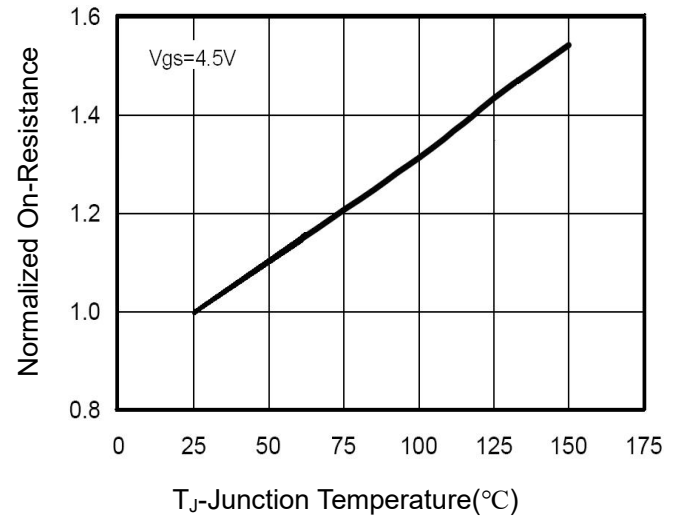


Figure 8 Drain-Source On-Resistance

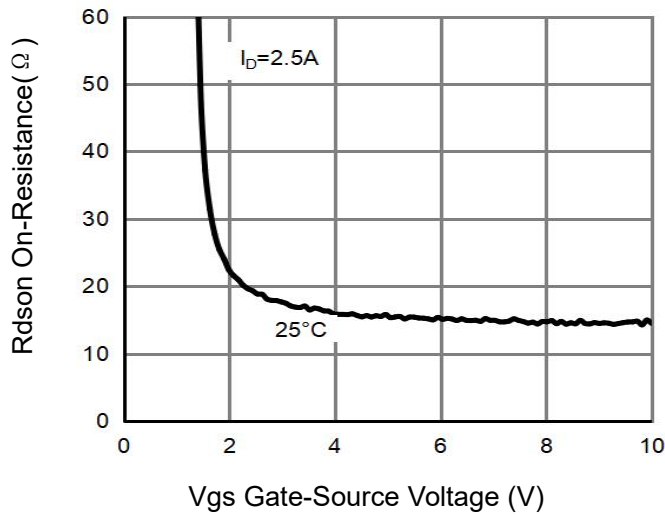


Figure 9 Rdson vs. Vgs

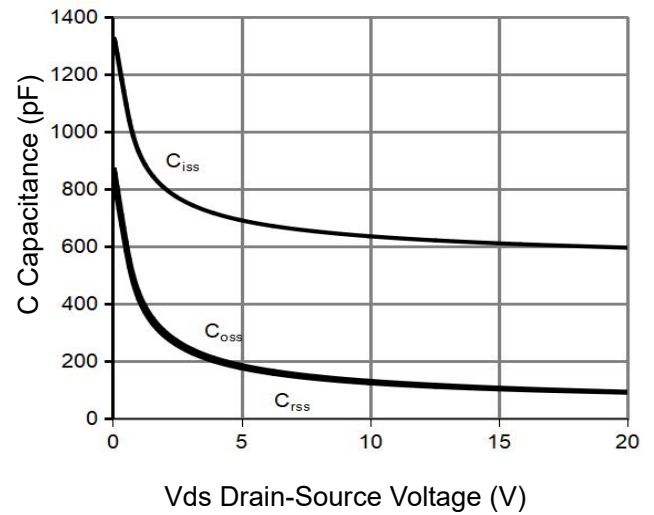


Figure 10 Capacitance vs Vds

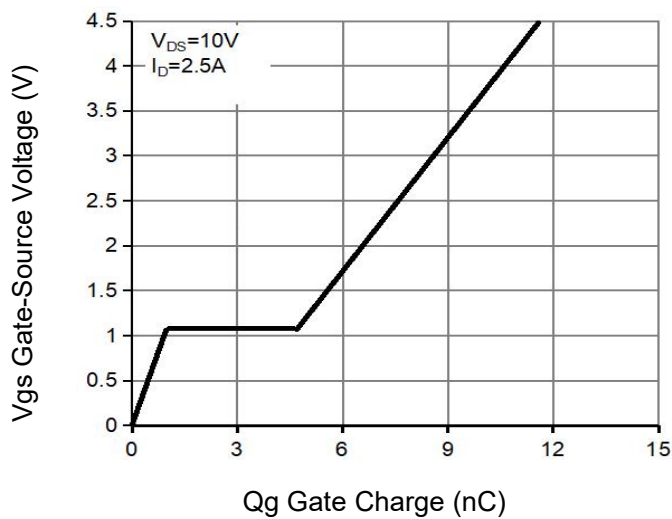


Figure 11 Gate Charge

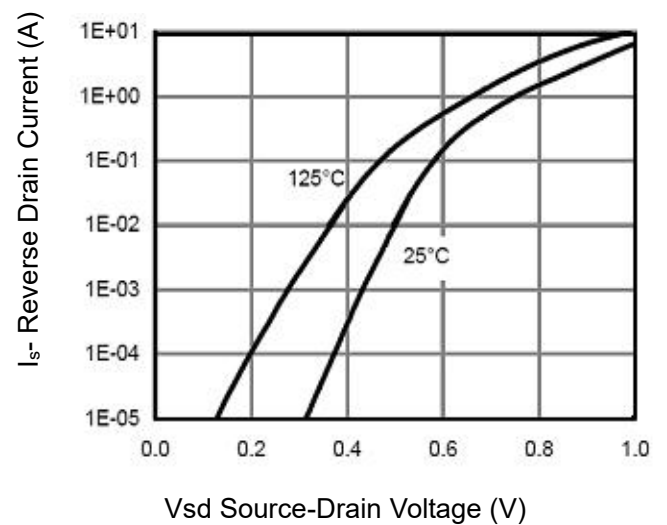


Figure 12 Source- Drain Diode Forward

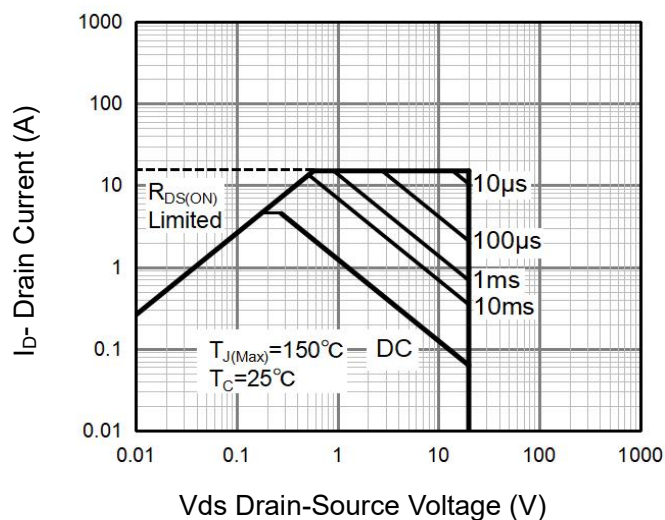


Figure 13 Safe Operation Area

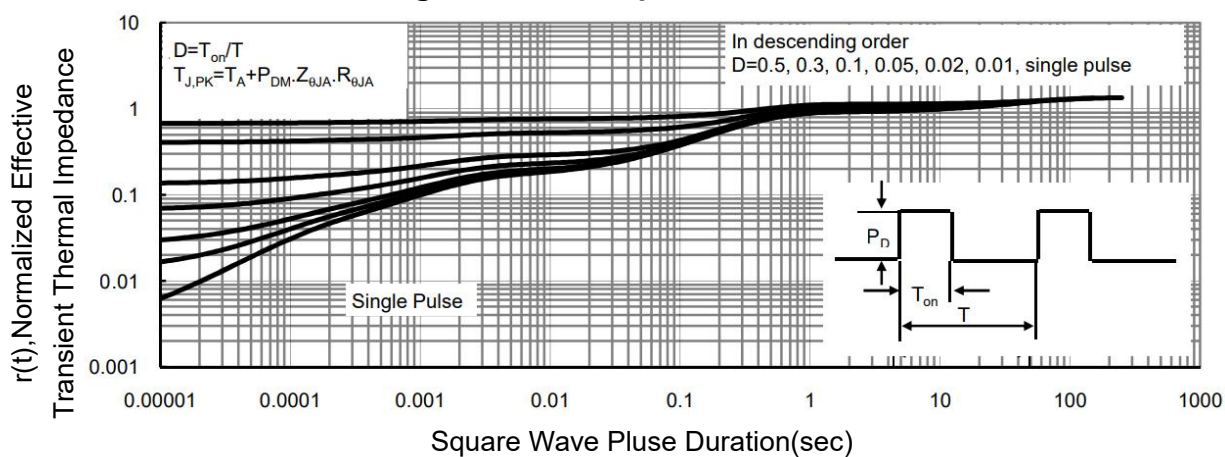
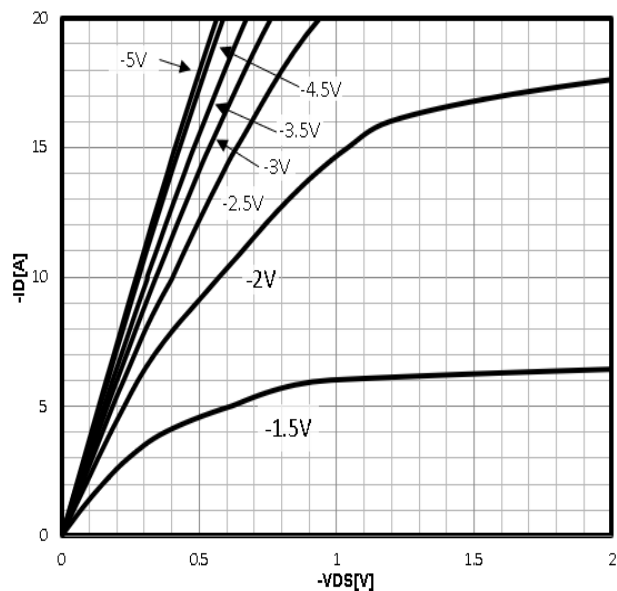


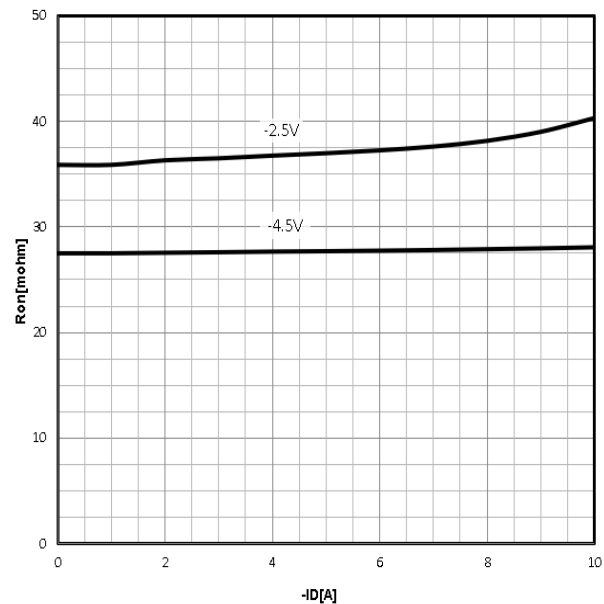
Figure 14 Normalized Maximum Transient Thermal Impedance

P-Channel Characteristics Curve:

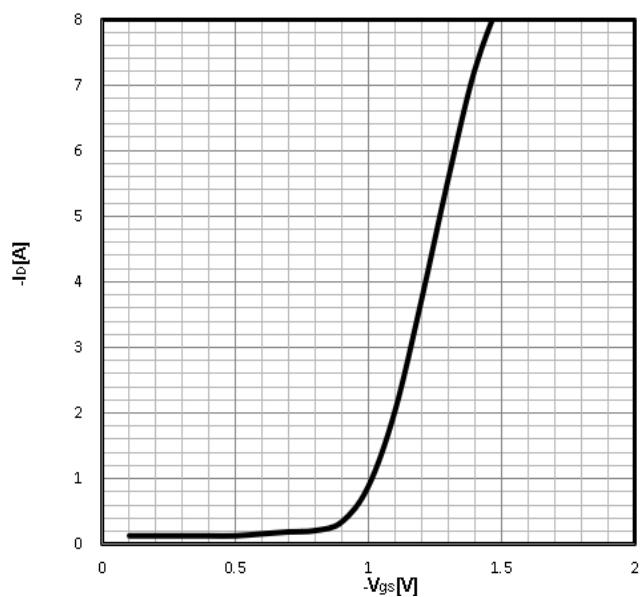
Typ. output characteristics
 $I_D = f(V_{DS})$



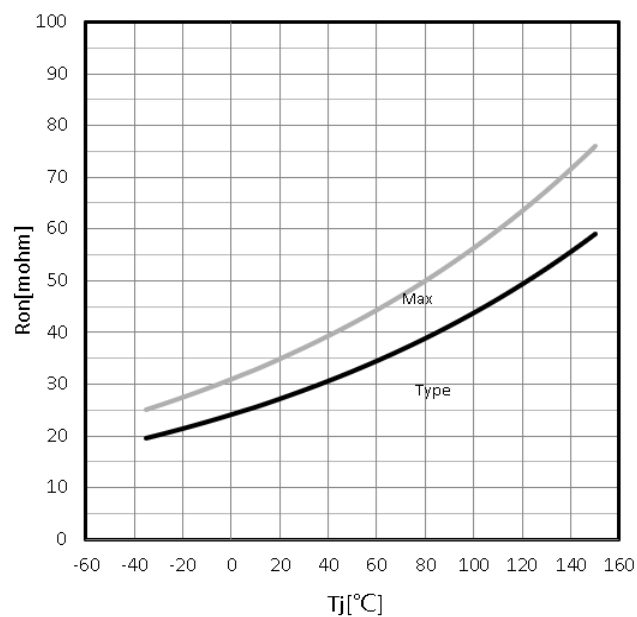
Typ. drain-source on resistance
 $R_{DS(on)} = f(I_D)$



Typ. transfer characteristics
 $I_D = f(V_{GS})$

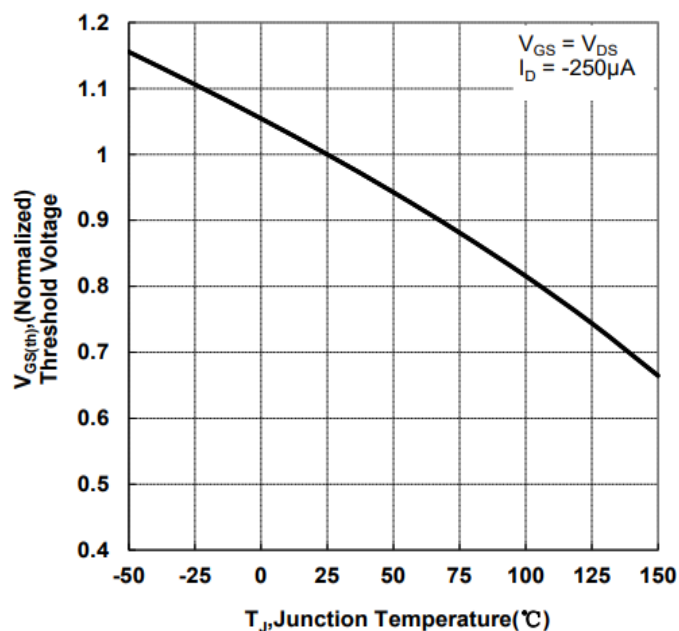


Drain-source on-state resistance
 $R_{DS(on)} = f(T_j); I_D = -4A; V_{GS} = -4.5V$



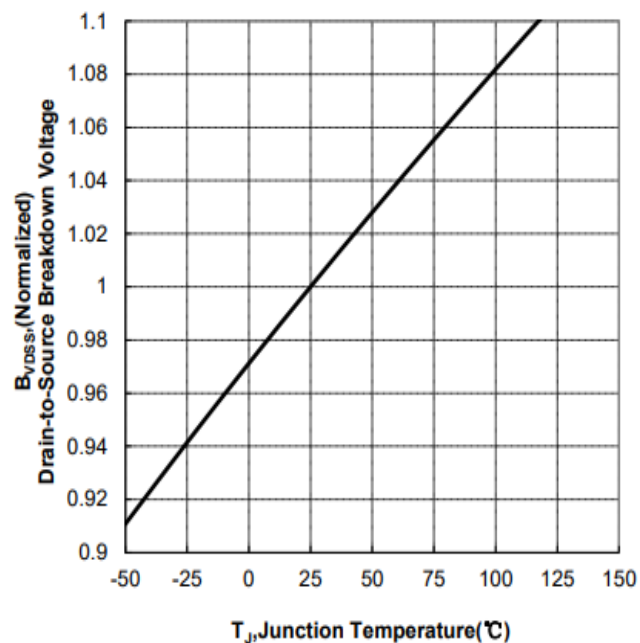
Gate Threshold Voltage

$$-V_{TH}=f(T_j); I_D=-250\mu A$$



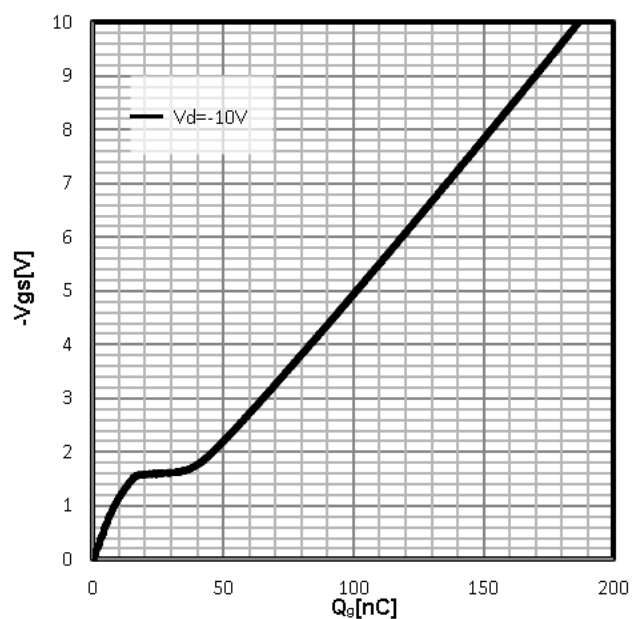
Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=-250\mu A$$



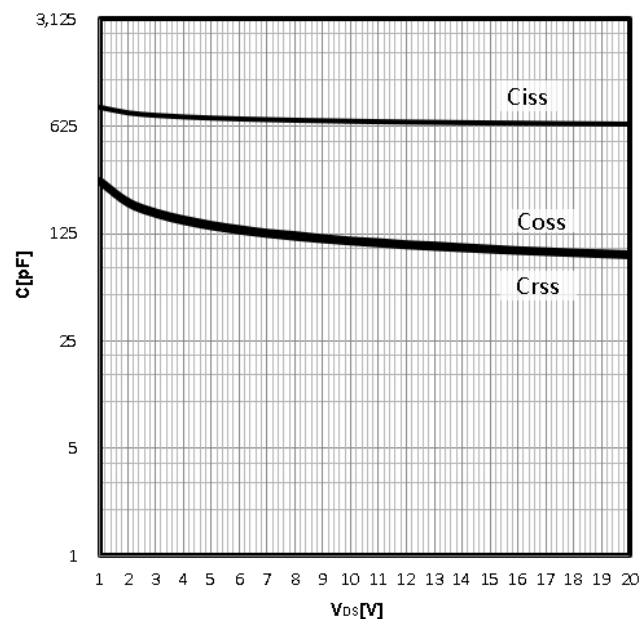
Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=-5A$$

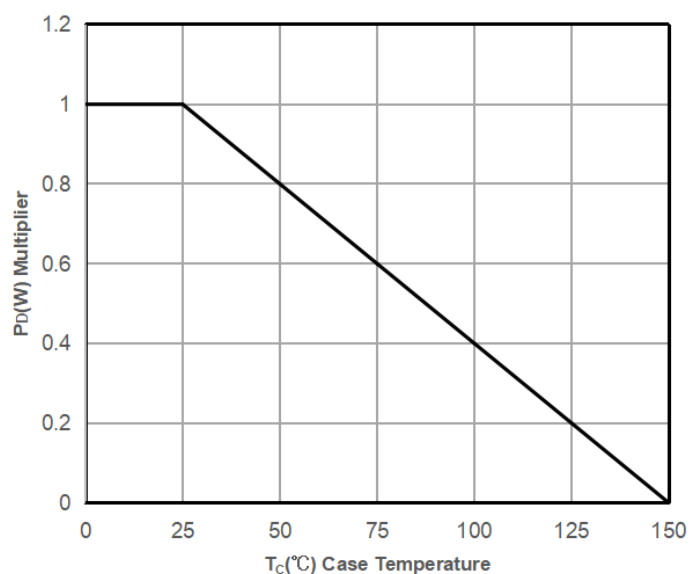


Typ. capacitances

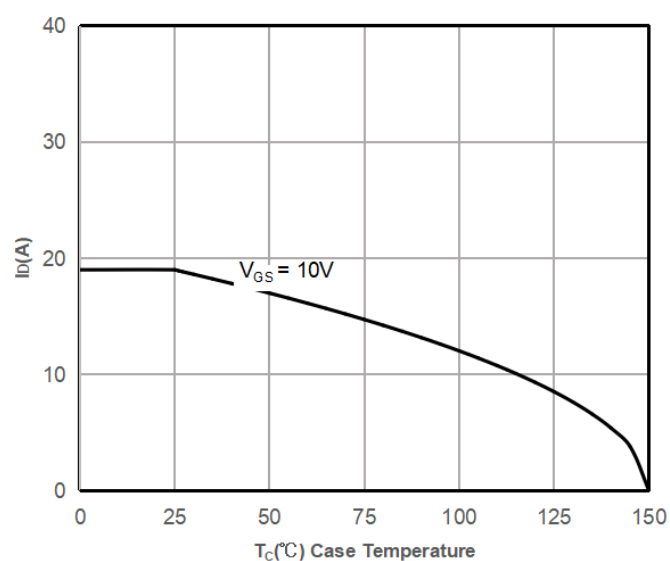
$$C=f(V_{DS}); V_{GS}=0V; f=1MHz$$



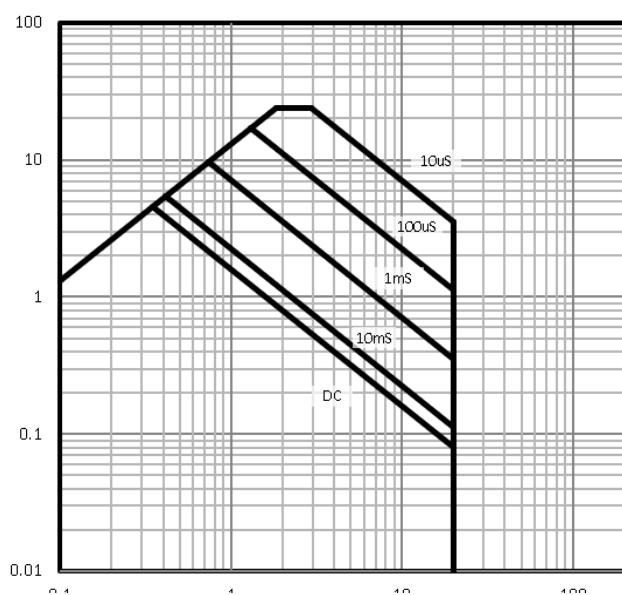
Power Dissipation
 $P_{tot}=f(T_C)$



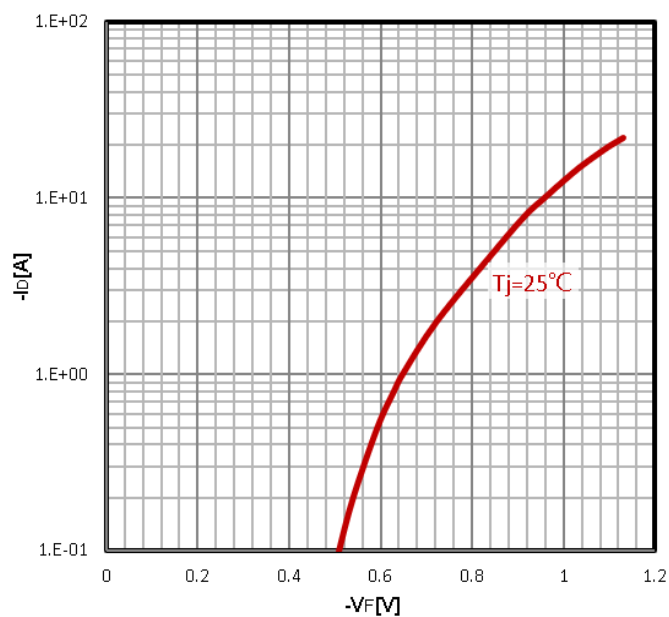
Maximum Drain Current
 $-I_D=f(T_C)$



Safe operating area
 $-I_D=f(-V_{DS})$

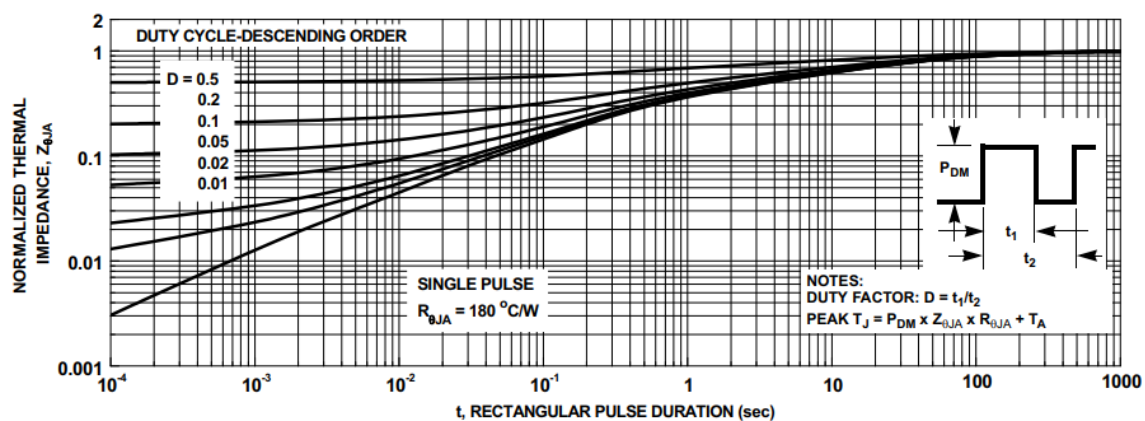


Body Diode Forward Voltage Variation
 $-I_F=f(-V_{DS})$

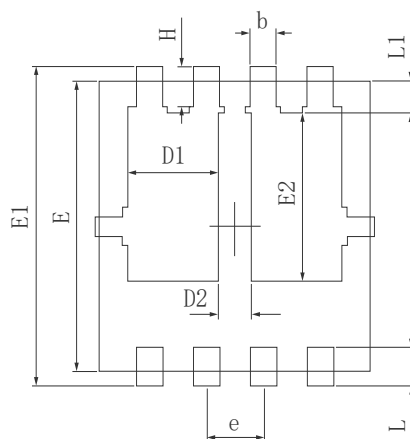
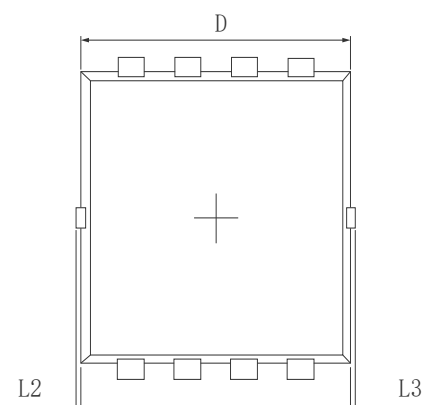


Max. transient thermal impedance

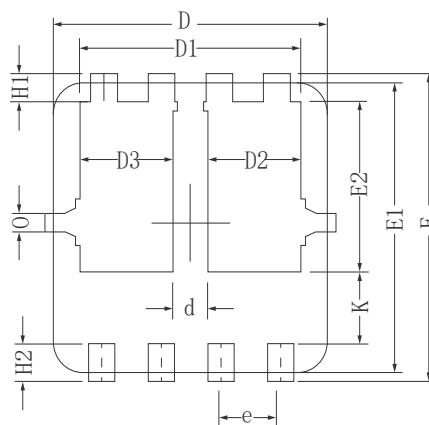
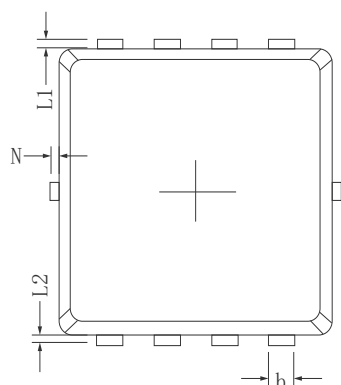
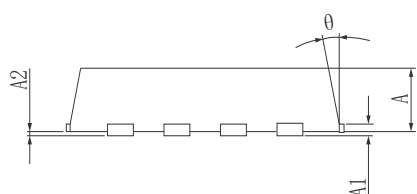
$$Z_{thJC}=f(t_p)$$



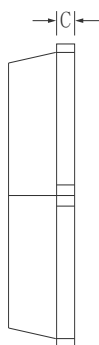
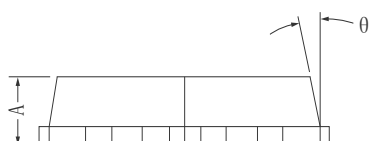
Dimensions (PDFN3.3*3.3)



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.700	0.900
A1	0.152REF.	
A2	0~0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0~0.100	
L3	0~0.100	
H	0.315	0.515
θ	8°	12°

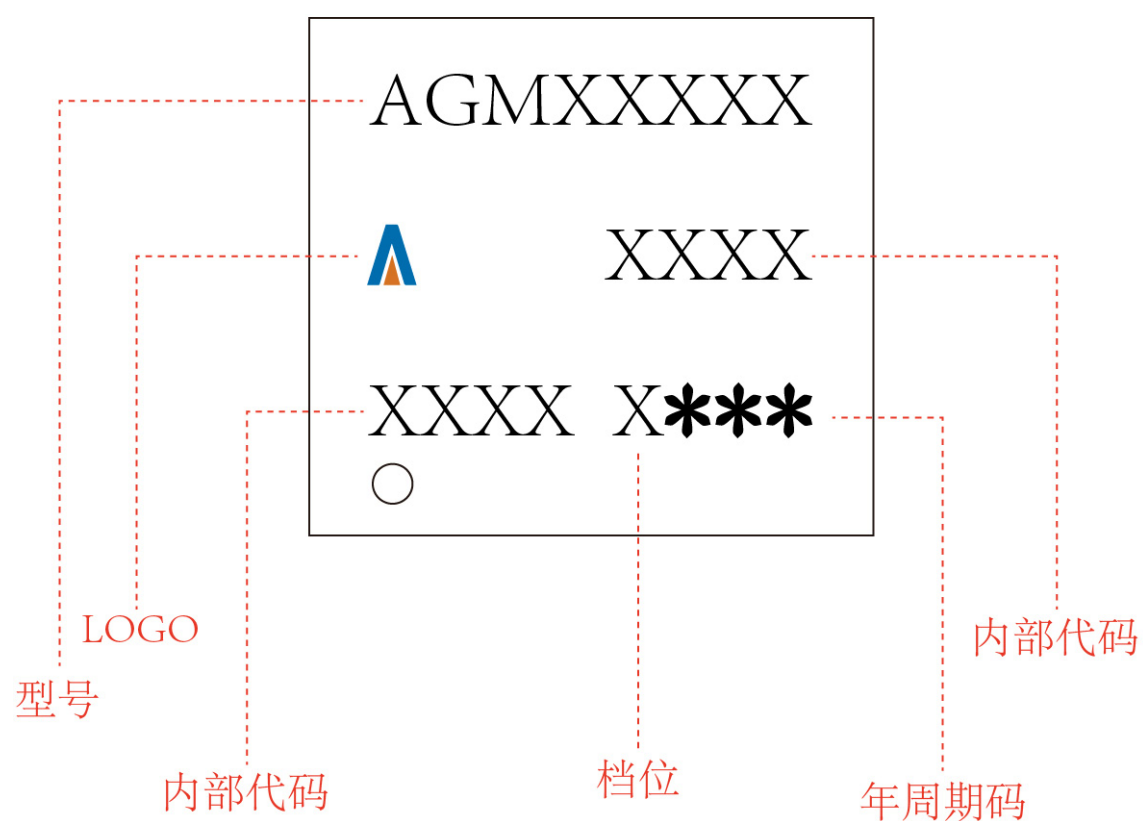


Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.65	0.75	0.85
b	0.25	0.30	0.35
C	0.15	0.20	0.25
D	3.00	3.10	3.20
D1	2.40	2.50	2.60
D2/D3	1.00	1.05	1.10
d	0.30	0.40	0.50
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	1.72	1.82	1.92
e	0.65 BSC.		
H1	0.21	0.31	0.41
H2	0.30	0.40	0.50
K	0.67	0.77	0.87
L1/L2	0.10 REF.		
θ	11°	12°	13°
N	0	-	0.15
0	0.2 REF.		



PDFN3.3*3.3

Marking Instructions:



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